

Titles of most frequently occurring classifications of patents returned
from a search of 10562839 on Dec 13 , 2007

- 5 257/E23.039 (0 OR, 5 XR)
 - Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
 - 257/E23.001 .PACKAGING, INTERCONNECTS, AND MARKINGS FOR SEMICONDUCTOR OR OTHER SOLID-STATE DEVICES (EPO)
 - 257/E23.01 ..Arrangements for conducting electric current to or from solid-state body in operation, e.g., leads, terminal arrangements (EPO)
 - 257/E23.023 ...Consisting of soldered or bonded constructions (EPO)
 - 257/E23.031Lead frames or other flat leads (EPO)
 - 257/E23.037Characterized by die pad (EPO)
 - 257/E23.039Chip-on-leads or leads-on-chip techniques, i.e., inner lead fingers being used as die pad (EPO)
- 4 257/E23.142 (0 OR, 4 XR)
 - Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
 - 257/E23.001 .PACKAGING, INTERCONNECTS, AND MARKINGS FOR SEMICONDUCTOR OR OTHER SOLID-STATE DEVICES (EPO)
 - 257/E23.141 ..Arrangements for conducting electric current within device in operation from one component to another, interconnections, e.g., wires, lead frames (EPO)
 - 257/E23.142 ...Including external interconnections consisting of multilayer structure of conductive and insulating layers inseparably formed on semiconductor body (EPO)
- 4 257/E21.507 (0 OR, 4 XR)
 - Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
 - 257/E21.001 .PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE OR TREATMENT OF SEMICONDUCTOR OR SOLID-STATE DEVICES OR OF PARTS THEREOF (EPO)
 - 257/E21.002 ..Manufacture or treatment of semiconductor device (EPO)
 - 257/E21.04 ...Device having at least one potential-jump barrier or surface barrier, e.g., PN junction, depletion layer, carrier concentration layer (EPO)
 - 257/E21.499Assembling semiconductor devices, e.g., packaging , including mounting, encapsulating, or treatment of packaged semiconductor (EPO)
 - 257/E21.506Attaching or detaching leads or other conductive members, to be used for carrying current to or from device in operation (EPO)
 - 257/E21.507Formation of contacts to semiconductor by use of metal layers separated by insulating layers, e.g., self-aligned contacts to source/drain or emitter/base (EPO)
- 4 257/E21.503 (0 OR, 4 XR)
 - Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
 - 257/E21.001 .PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE OR TREATMENT OF SEMICONDUCTOR OR SOLID-STATE DEVICES OR OF PARTS THEREOF (EPO)
 - 257/E21.002 ..Manufacture or treatment of semiconductor device (EPO)
 - 257/E21.04 ...Device having at least one potential-jump barrier or surface barrier, e.g., PN junction, depletion layer, carrier concentration layer (EPO)
 - 257/E21.499Assembling semiconductor devices, e.g., packaging , including mounting, encapsulating, or treatment of packaged semiconductor (EPO)
 - 257/E21.502Encapsulation, e.g., encapsulation layer, coating (EPO)
 - 257/E21.503Encapsulation of active face of flip chip device, e.g., under filling or under encapsulation of flip-chip, encapsulation perform on chip or mounting substrate (EPO)
- 4 257/E27.111 (0 OR, 4 XR)
 - Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)
 - 257/E27.001 .DEVICE CONSISTING OF A PLURALITY OF SEMICONDUCTOR OR OTHER SOLID STATE COMPONENTS FORMED IN OR ON A COMMON SUBSTRATE, E.G., INTEGRATED CIRCUIT DEVICE

(EPO)

257/E27.009 ..Including semiconductor component with at least one potential barrier or surface barrier adapted for rectifying, oscillating, amplifying, or switching, or Including integrated passive circuit elements (EPO)

257/E27.111 ...Substrate comprising other than a semiconductor material, e.g. insulating substrate or layered substrate Including a non-semiconductor layer (EPO)

3 257/341 (2 OR, 1 XR)

Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)

257/213 .FIELD EFFECT DEVICE

257/288 ..Having insulated electrode (e.g., MOSFET, MOS diode)

257/327 ...Short channel insulated gate field effect transistor

257/335Active channel region has a graded dopant concentration decreasing with distance from source region (e.g., double diffused device, DMOS transistor)

257/341Plural sections connected in parallel (e.g., power MOSFET)

3 257/620 (0 OR, 3 XR)

Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)

257/618 .PHYSICAL CONFIGURATION OF SEMICONDUCTOR (E.G., MESA, BEVEL, GROOVE, ETC.)

257/620 ..With peripheral feature due to separation of smaller semiconductor chip from larger wafer (e.g., scribe region, or means to prevent edge effects such as leakage current at peripheral chip separation area)

3 257/E29.066 (0 OR, 3 XR)

Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)

257/E29.001 .SEMICONDUCTORS DEVICES ADAPTED FOR RECTIFYING, AMPLIFYING, OSCILLATING, OR SWITCHING, CAPACITORS, OR RESISTORS WITH AT LEAST ONE POTENTIAL-JUMP BARRIER OR SURFACE BARRIER (EPO)

257/E29.002 ..Electrical characteristics due to properties of entire semiconductor body rather than just surface region (EPO)

257/E29.005 ...Characterized by specified shape or size of PN junction or by specified impurity concentration gradient within the device (EPO)

257/E29.043With semiconductor regions connected to electrode not carrying current to be rectified, amplified or switched and such electrode being part of semiconductor device which comprises three or more electrodes (EPO)

257/E29.066Body region structure of IGFET's with channel containing layer (DMOSFET or IGBT) (EPO)

3 257/E29.257 (0 OR, 3 XR)

Class 257 ACTIVE SOLID-STATE DEVICES (E.G., TRANSISTORS, SOLID-STATE DIODES)

257/E29.001 .SEMICONDUCTORS DEVICES ADAPTED FOR RECTIFYING, AMPLIFYING, OSCILLATING, OR SWITCHING, CAPACITORS, OR RESISTORS WITH AT LEAST ONE POTENTIAL-JUMP BARRIER OR SURFACE BARRIER (EPO)

257/E29.166 ..Types of semiconductor device (EPO)

257/E29.169 ...Controllable by only signal applied to control electrode (e.g., base of bipolar transistor, gate of field-effect transistor) (EPO)

257/E29.226Unipolar device (EPO)

257/E29.242Field-effect transistor (EPO)

257/E29.255With field effect produced by insulated gate (EPO)

257/E29.256With channel containing layer contacting drain drift region (e.g., DMOS transistor) (EPO)

257/E29.257Having vertical bulk current component or current vertically following trench gate (e.g., vertical power DMOS transistor) (EPO)

3 372/46.01 (2 OR, 1 XR)

Class 372 COHERENT LIGHT GENERATORS

372/39 .PARTICULAR ACTIVE MEDIA

372/43.01 ..Semiconductor